

### AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Cancelled)
2. (Currently Amended) [[The method of claim 1,]] A method comprising:  
  
reducing a height of a plurality of roughness formations on a surface of a film over a semiconductor substrate by exposing the film to a smoothing medium,  
  
wherein the roughness formations have a first height before said exposure and a second height after said exposure, the second height being less than the first height.
3. (Original) The method of claim 2, further comprising removing the film from the smoothing medium.
4. (Currently Amended) The method of claim 3, wherein the film [[is]] comprises a copolymer.
5. (Original) The method of claim 4, wherein the copolymer comprises at least one of Vinylidene Fluoride and Trifluoroethylene.
6. (Currently Amended) The method of claim 5, wherein the semiconductor substrate [[is]] comprises a semiconductor wafer.
7. (Currently Amended) The method of claim 6, further comprising forming the film [[on]] over the semiconductor wafer, said [[formation]] forming occurring while the semiconductor wafer is spun.

8. (Currently Amended) The method of claim 7, wherein the smoothing medium comprises a solvent.
9. (Currently Amended) The method of claim 8, wherein the solvent comprises ethyl lactate.
10. (Currently Amended) A method comprising:
- dispensing a smoothing solvent onto a film over a semiconductor substrate, the film having a plurality of roughness formations on a surface thereof, the roughness formations having a first height; and
- removing the smoothing solvent from the film, the roughness formations having a second height after said removal, the second height being less than the first height.
11. (Currently Amended) The method of claim 10, wherein the film comprises a spun film.
12. (Currently Amended) The method of claim 11, wherein the film comprises a copolymer.
13. (Currently Amended) The method of claim 12, wherein the semiconductor substrate comprises a wafer.
14. (Original) The method of claim 13, wherein the wafer is spun to remove the smoothing solvent.
15. (Currently Amended) A method comprising:
- spinning a semiconductor wafer about a central axis thereof;

dispensing a polymer on the semiconductor wafer during said spinning to form a polymeric film thereon, the polymeric film having a plurality of roughness formations on a surface thereof, the roughness formations having a first height;

heating the semiconductor wafer;

dispensing a smoothing solvent onto the film; and

removing the smoothing solvent from the film by spinning the semiconductor wafer about the central axis thereof, the roughness formations having a second height after said removal, the second height being less than the first height.

16. (Original) The method of claim 15, wherein the central axis of the wafer is perpendicular to an upper surface thereof.

17. (Currently Amended) The method of claim 16, wherein the polymer ~~[[is]]~~ comprises a copolymer.

Claims 18-27 (Cancelled)

28. (New) The method of claim 2, wherein said exposing the film to the smoothing medium comprises allowing a puddle of solvent to stand on the film.

29. (New) The method of claim 28, wherein said allowing the puddle of solvent to stand on the film comprises allowing the puddle of solvent to stand on the film for at least five minutes.

30. (New) The method of claim 2, further comprising:

forming an electrode over the film after said reducing the height of the plurality of roughness formations; and

programming a portion of the film to hold a bit by using the electrode.

31. (New) The method of claim 2, wherein the film comprises a ferroelectric polymer.

32. (New) The method of claim 10, further comprising allowing a puddle of the smoothing solvent to stand on the film.

33. (New) The method of claim 10, wherein the film comprises a ferroelectric polymer, further comprising forming an electrode over the film after said removing the smoothing solvent from the film.